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DERWENT-WEEK: 200441

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TITLE: Method for manufacturing capacitor of feram

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KR 418585 B 021/8242	February 14, 2004	N/A	000	H01L
KR 2003002048 A	January 8, 2003	N/A	001	H01L 021/8242

APPLICATION-DATA:

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KR 418585B	N/A	2001KR-0038783	June 30, 2001
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ABSTRACTED-PUB-NO: KR2003002048A

BASIC-ABSTRACT:

NOVELTY - A method for manufacturing a capacitor of FeRAM is provided to prevent a damage between a lower insulating layer and a plug in a wet-etching by forming a lower electrode using an ECD(Electro-Chemical Deposition).

DETAILED DESCRIPTION - A contact hole is formed by selectively etching an

interlayer dielectric(140) formed on a semiconductor substrate(100) having a transistor. A contact plug(145a) is formed in the contact hole. A tungsten nitride(WNx) layer(160a) is formed on the interlayer dielectric so as to connect with the contact plug(145a). A platinum seed pattern(165) is formed on the WNx layer(160a). After forming a sacrificial layer on the resultant structure, the platinum seed pattern is exposed by selectively etching the sacrificial layer. A platinum lower electrode(175a) is formed on the exposed platinum seed pattern(165) by using an ECD method. After removing the sacrificial layer, a dielectric film(180) and an upper electrode(185) are sequentially formed on the lower electrode.

CHOSEN-DRAWING: Dwg.1/10

TITLE-TERMS: METHOD MANUFACTURE CAPACITOR

DERWENT-CLASS: L03 U11 U12 U13

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